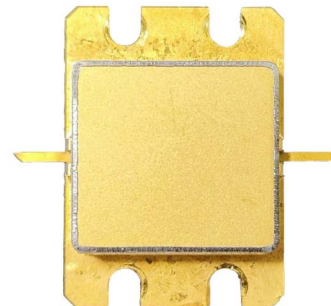


## Description

LNPA2530-150 is a gallium nitride high electron mobility transistor (GaN HEMT). It is a high-power internally matched power transistor that can operate in pulse mode at saturated power. It is used in standard communication and radar frequency bands in 50Ω systems. Provides optimal power and gain performance.



## Features

- Coverable working frequency band range: 2.55~3.0GHz
- Good 50Ω impedance matching, easy to use in cascade
- Metal ceramic shell sealed package
- Available in screw-on flange package or welded pill package

## Limit parameters

- Source-drain voltage  $V_{ds}$ : +100V
- Gate-source voltage  $V_{gs}$ : -10V
- Dissipated power ( $T_c=25^\circ\text{C}$ ): 89W
- Storage temperature:  $-55^\circ\text{C}\sim+125^\circ\text{C}$
- Operating temperature:  $-40^\circ\text{C}\sim+75^\circ\text{C}$

## Electrical performance table

Working conditions: 50Ω test system,  $T_A = +25^\circ\text{C}$ ,  $V_{DS}=+28\text{V}$ ,  $I_{DS}=300\text{mA}$ , CW.

Parameter	Test Conditions		Min.	Typ.	Max.	Units
Saturation power	Freq.=2.55GHz~3.0GHz $V_{GS}=-2.0\sim-3.0\text{V}$ $V_{DS}=+28\text{V}$ $I_{DSq}=250\text{mA}$		-	52	-	dBm
power gain			-	11.5	-	dB
power added efficiency			54.8	-	-	%
power flatness			-	-	0.5	dB
Pinch-off voltage	$V_{DS}=6\text{V}$	$I_{DS}\leq 100\text{mA}$	-5	-	-3.5	V
Gate-source reverse current	$V_{DS}=0\text{V}$	$V_{GS}=-10\text{V}$	-	-	5	uA

Products with similar power specifications, higher efficiency and wider frequency bands can be customized.

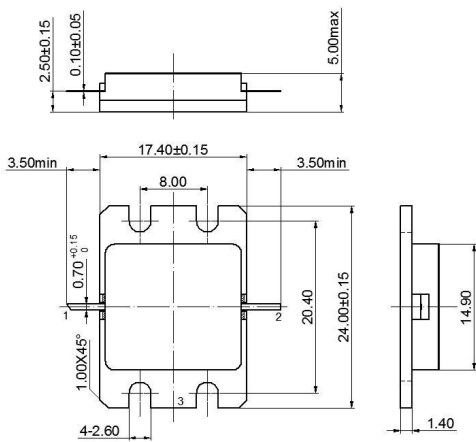
Indicator test

1.Test conditions: TA = +25°C, VDS=+28V, IDS=80mA, duty cycle D=10%, pulse width  $\tau$  =200us.

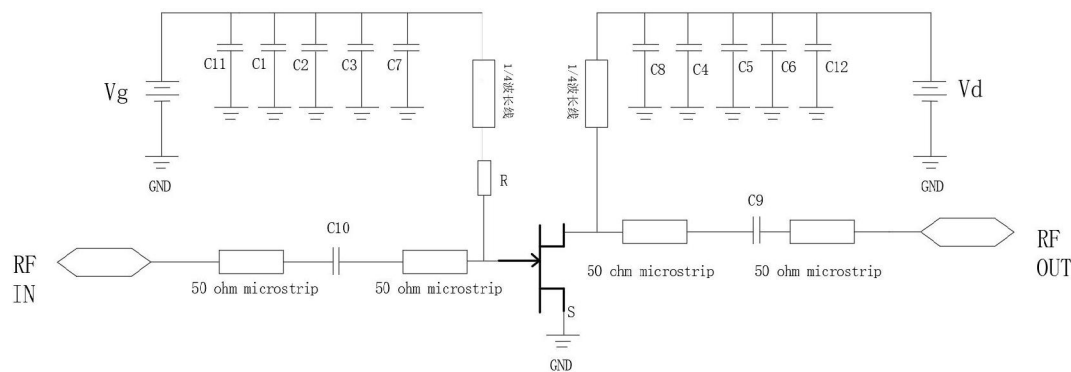
(GHz)	Input power (dBm)	Output Power (dBm)	Gain (dB)	efficiency (%)	IMD3(dBc, Pout=48dBm)	Second harmonic suppression (dBc)
2.55	38.5	51.85	12.35	57.2	-21	-32
2.65	38.5	52	12.5	61.1	-20.5	-40
2.75	38.5	51.8	12.3	64.3	-20	-47
2.85	38.5	51.7	12.2	60.4	-20	-56
2.95	38.5	51.5	12	58.4	-20	-54
3	38.5	51.5	12	56.2	-20	-51

Dimensional drawing

Note: The unit in the figure is millimeters (mm), polarity: chamfered end - gate; flat angle end - drain.



Recommended application circuit diagram



C7, C8, C9, C10	10pF	0805
C3, C4	1000pF	0805
C2, C5	10nF	0805
C1, C6	4.7 $\mu$ F	0805
C11	47 $\mu$ F	
C12	470 $\mu$ F	
R	20 $\Omega$	0805
PCB	5880	Rogers
PCB thickness	0.508mm	
Dielectric constant	2.2	

Precautions

1. This device is an internal matching device with an input and output impedance of 50 $\Omega$ .
2. When powering up, please strictly follow the order of first negative pressure and then positive pressure; when powering on, add the gate voltage first, then add the leakage voltage; when powering off, first reduce the leakage voltage, then reduce the grid voltage.
3. Pay attention to heat dissipation during use. The lower the temperature of the tube and shell, the longer the service life of the device.
4. During use, instruments, equipment, etc. should be well grounded; this product is an electrostatic sensitive device, so pay attention to anti-static when storing and using it.

Please select the power supply reasonably according to the specific modulation method and corresponding requirements.